In response to the Office Action dated March 4, 2003 kindly amend the subject application as follows:

b.) Amendments to the Specification:

Please amend the specification on page 80, lines 7-19 to read as follows:

-- Examples of the mechanical impact application apparatus may include:

mechanical pulverizers, such as Krypron System "KRYOPRON SYSTEM" (made by
Kawasaki Jukogyo K.K.) and "Trubomill" "TURBOMILL" (made by Turbo Kogyo K.K.),
and mechanical impacting devices, such as "Mechanofusion System"

"MECHANOFUSION SYSTEM" (made by Nara Kikai Seisakusho K.K.) and
"Hybridization System" "HYBRIDIZATION SYSTEM" (made by Nara Kikai Seisakusho
K.K.) wherein toner particles are pressed against an inner wall of a casing under action of a centrifugal force exerted by blades stirring at high speeds, thereby applying mechanical impact forces including compression and abrasion forces to the toner particles. --

Please amend the specification on page 108, line 6 to page 109, line 11 to read as follows:

- The particle size distributions and average particle sizes may be measured by using, e.g., Coulter Counter Model TA-II or Coulter Multicizer MULTISIZER (respectively available from Coulter Electronics, Inc.). Herein, these values are determined based on values measured by using Coulter Multicizer MULTISIZER connected to an interface (made by Nikkaki K.K.) and a personal computer ("PC9801", made by NEC K.K.) for providing a number-basis distribution and a volume-basis distribution in the following manner. A 1%-



aqueous solution is prepared as an electrolytic solution by sing a reagent-grade sodium chloride (it is also possible to use ISOTON R-II (available from Coulter Scientific Japan K.K.)). For the measurement, 0.1 to 5 ml of a surfactant, preferably a solution of an alkylbenzenesulfonic acid salt, is added a a dispersant into 100 to 150 ml of the electrolytic solution, and 2-20 mg of a sample toner is added thereto. The resultant dispersion of the sample in the electrolytic solution is subjected to a dispersion treatment for ca. 1-3 minutes by means of an ultrasonic disperser, and then subjected to measurement of particle size distribution in the range of 2.00 - $40.30~\mu m$ divided into 13 channels by using the abovementioned Coulter counter with a $100~\mu m$ - aperture to obtain a volume-basis distribution and a number-basis distribution. From the volume-basis distribution, a weight-average particle size (D4) and a volume-average particle size (Dv) are calculated by using a central value as a representative value channel. From the number-basis distribution, a number-average particle size (D1) and a number-basis variation coefficient (S1) is calculated.-

Please amend the specification on page 119, lines 9-12 to read as follows:

- - The cells may preferably have concavities providing an average cell diameter corresponding to spheres of 5 - 300 μm and also a void <u>areal</u> percentage at the surface of 15 - 90 %.- -

Please amend the specification on page 130, line 23 to page 131, line 4 to read as follows:



- The AC voltage may preferably have a peak voltage of blow below 2 x Vth (Vth: discharge initiation voltage at the time of DC voltage application). If this condition is not satisfied, the potential on the image-bearing member is liable to be unstable. The AC voltage applied in superposition with a DC voltage may more preferably have a peak

CV

voltage below Vth so as to charge the image-bearing member without being substantially accompanied with a discharge phenomenon. - -

Please amend the specification on page 133, line 26 to page 134, lines 5 to read as follows:



- The classification method and apparatus used for production of magnetic particles are not particularly limited. In order to obtain a desired particle size efficiently, it is preferred use a sloped inertia classifier such as "Elbow Jet" "ELBOW JET", a centrifugal separator separator, such as "Dispersion Separator" "DISPERSION

SEPARATOR" or "Turboplex" "TURBOPLEX", or sieving.--

Please amend the specification on page 148, lines 6 - 10 to read as follows:

- - During the formation of the photoconductor layer 203, the electroconductive support 21 201 may be held at an optimally set temperature, preferably 200 - 350 °C, more preferably 230 - 330 °C, further preferably 250 - 310 °C. - -

Please amend the specification on page 148, line 26 to page 149, line 10 to read as follows:



- The surface layer 24 204 may comprise any non-single crystal material. For example, the surface layer may comprise: amorphous silicon containing hydrogen (H) and/or halogen (X) and further carbon (C) (denoted by "a-SiC:H,X"), amorphous silicon containing hydrogen (H) and/or halogen (X) and further oxygen (O) (denoted by "a-SiO:H,X"), amorphous silicon containing hydrogen (H) and/or halogen (X and further nitrogen (N) (denoted by "a-SiN:H,X"), and amorphous silicon containing hydrogen (H) and/or halogen (X) and further at least one of carbon (C), oxygen (O) and nitrogen (N) (denoted by "a-SiCON:H,X").- -

Please amend the specification on page 160, line 26 to page 161, line 12, to read as follows:

-- The surface roughness (Ra) values described herein are based on values measured as center line-average roughness values by using a surface roughness meter ("Surfcorder SE-3OH" "SURFCORDER SE-3OH", available from K.K. Kosaka Kenkyusho) according to JIS B-0601. More specifically, based on a surface roughness curve obtained for a sample surface, a length of a is taken along a center line of the roughness curve. The roughness curve is represented by a function Y = f(x) while setting the X-axis on the center line and a roughness scale (y) on the Y-axis along the length x portion. A center line-average roughness Ra of the roughness curve is determined by the following formula:-